- *EPIC*<sup>TM</sup> (Enhanced-Performance Implanted CMOS) Submicron Process
- I<sub>off</sub> Feature Supports Partial-Power-Down Mode Operation
- Supports 5-V V<sub>CC</sub> Operation
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages

### description

This single bus buffer gate is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

The SN74LVC1G126 is a single bus driver/line driver with a 3-state output. The output is disabled when the output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC1G126 is characterized for operation from -40°C to 85°C.

INPU	JTS	OUTPUT
OE	Α	Y
н н		Н
н	L	L
L	Х	Z

**FUNCTION TABLE** 

### logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

### logic diagram (positive logic)





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SN74LVC1G126

SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES224C - APRIL 1999 - REVISED FEBRUARY 2000

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

$ \begin{array}{llllllllllllllllllllllllllllllllllll$	6.5 V 0.5 V 50 mA 50 mA 50 mA 00 mA 00 mA 7°C/W 9°C/W
Storage temperature range, I <sub>stg</sub>	150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The value of  $V_{CC}$  is provided in the recommended operating conditions table.

3. The package thermal impedance is calculated in accordance with JESD 51.

### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT			
\/	Cupply voltogo	Operating	1.65	5.5	V			
VCC	Supply voltage	Data retention only	1.5		v			
	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$					
\ <i>\</i>		$V_{CC}$ = 2.3 V to 2.7 V	1.7		v			
VIH		$V_{CC} = 3 V \text{ to } 3.6 V$	2		V			
		$V_{CC}$ = 4.5 V to 5.5 V						
		V <sub>CC</sub> = 1.65 V to 1.95 V		$0.35 \times V_{CC}$				
N/		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	v			
VIL	Low-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$		0.8				
		V <sub>CC</sub> = 4.5 V to 5.5 V		$0.3 \times V_{CC}$				
VI	Input voltage	•	0	5.5	V			
VO	Output voltage		0	V <sub>CC</sub>	V			
		V <sub>CC</sub> = 1.65 V		-4				
	High-level output current	V <sub>CC</sub> = 2.3 V		-8				
IOH				-16	mA			
		VCC = 3 V		-24				
		V <sub>CC</sub> = 4.5 V		-32				
	Low-level output current $V_{CC} = V_{CC}$	V <sub>CC</sub> = 1.65 V		4				
		V <sub>CC</sub> = 2.3 V		8				
IOL		N 2 N		16	mA			
		vCC = 3 v		24				
		V <sub>CC</sub> = 4.5 V						
	Input transition rise or fall rate	V <sub>CC</sub> = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20				
$\Delta t/\Delta v$		V <sub>CC</sub> = 3.3 V ± 0.3 V		10	ns/V			
		$V_{CC} = 5 V \pm 0.5 V$		5				
TA	Operating free-air temperature		-40	85	°C			

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



## SN74LVC1G126 SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

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PAR	RAMETER TEST CONDITIONS		VCC	MIN	TYP†	MAX	UNIT	
		I <sub>OH</sub> = -100 μA	1.65 V to 5.5 V	V <sub>CC</sub> -0.1			V	
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
		$I_{OH} = -8 \text{ mA}$	2.3 V	1.9				
VOH		I <sub>OH</sub> = -16 mA		2.4				
		$I_{OH} = -24 \text{ mA}$	3 V	2.3				
		I <sub>OH</sub> = -32 mA	4.5 V	3.8				
		I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.1		
		$I_{OL} = 4 \text{ mA}$	1.65 V			0.45		
		I <sub>OL</sub> = 8 mA	2.3 V			0.3		
VOL		I <sub>OL</sub> = 16 mA				0.4	- V	
		I <sub>OL</sub> = 24 mA	3 V			0.55		
		I <sub>OL</sub> = 32 mA	4.5 V			0.55		
II A or OE inputs		$V_{I} = 5.5 V \text{ or GND}$	0 to 5.5 V			±5	μΑ	
loff		$V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	0			±10	μA	
IOZ		$V_{O} = 0$ to 5.5 V	3.6 V			10	μA	
ICC		$V_{I} = 5.5 \text{ V or GND}, \qquad I_{O} = 0$	1.65 V to 5.5 V			10	μΑ	
∆ICC		One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND	3 V to 5.5 V			500	μΑ	
Ci		$V_{I} = V_{CC} \text{ or } GND$	3.3 V				pF	

### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

F	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V ± 0.15 V				V <sub>CC</sub> = 2.5 V ± 0.2 V			V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V	
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
	<sup>t</sup> pd	A	Y									ns		
	<sup>t</sup> en	OE	Y									ns		
	<sup>t</sup> dis	OE	Y									ns		

## operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS			V <sub>CC</sub> = 3.3 V		UNIT
			TYP	TYP	ITP	TYP	
Cpd	Power dissipation capacitance	f = 10 MHz					pF





- NOTES: A. CL includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
    C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>Q</sub> = 50 Ω, t<sub>f</sub> ≤ 2 ns, t<sub>f</sub> ≤ 2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLZ and tpHZ are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tPLH and tPHL are the same as tpd.

### Figure 1. Load Circuit and Voltage Waveforms





- NOTES: A. CL includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2 ns, t<sub>f</sub>  $\leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.

  - E. tpLz and tpHz are the same as tdis.
  - F. tpzL and tpzH are the same as ten. G. tpl H and tpHI are the same as tpd.

### Figure 2. Load Circuit and Voltage Waveforms







NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
   Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 3. Load Circuit and Voltage Waveforms





NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis. F. tp71 and tp7H are the same as ten.
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

### Figure 4. Load Circuit and Voltage Waveforms





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